## Highly Crystalline Ni/NiO Hybrid Electrodes Processed by Inkjet Printing and Laser-Induced Reductive Sintering under Ambient Conditions

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**S1.** Summary of comparing existing solution-processed Ni or NiO thin film deposition methods along with their respective performance in literature

Author	Material	Process	Designated electrode	Feature Resolution (L: line width, F: film thickness)	Specific Resistivity (nΩ·m)
Liu et al. <sup>1*</sup>	Ni ion precursor	Spin coating <sup>a</sup> Oven sintering <sup>b</sup>	NiO	L: not applicable F: ~ 40 nm	None
Huang et al. <sup>2*</sup>	50 nm NiO particles	Inkjet printing <sup>a</sup>	NiO	L: not reported F: ~ 16 μm	1.13×10 <sup>11</sup>
Li et al. <sup>3*</sup>	Ni ion precursor	Reactive inkjet printing <sup>a</sup>	Ni	L: ~ 200 μm F: 5–10 μm	4.62×10 <sup>4</sup>
Lee et al.4*	3 nm NiO particles	Spin coating <sup>a</sup> Laser reductive sintering <sup>b</sup>	Ni	L: 6.5 μm F: 35–40 nm	6.30×10 <sup>2</sup>
This work	3 nm NiO particles	Inkjet printing <sup>a</sup> NiO: Oven Sintering <sup>b</sup> Ni: Laser reductive sintering <sup>b</sup>	NiO or Ni	NiO: L: ~ 50 μm, F: ~ 300 nm Ni: L: ~ 5 μm, F: ~100 nm (single line)	Ni: 1.03×10 <sup>3</sup>

<sup>a</sup> Material deposition method

<sup>b</sup> Subsequent annealing method

\* The reference is also cited in the main manuscript.

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